

IN THE ABSTRACT

Please amend the Abstract as follows:

Please amend the paragraph at page 60, lines 3-11, as follows:

A magnetic memory includes[[:]] a magnetoresistance effect element having a magnetic recording layer[[:]], a first wiring extending in a first direction on or below the magnetoresistance effect element[[:]], a covering layer provided on at least both sides of the first wiring[[:]], ~~the covering layer being made of magnetic material, and the covering layer having a uniaxial anisotropy in the first direction along which a magnetization of the covering layer occurs easily;~~ and a writing circuit configured to pass a current through the first wiring in order to record [[an]] information in the magnetic recording layer by a magnetic field generated by the current. The covering layer is made of magnetic material and has a uniaxial anisotropy in the first direction, along which a magnetization of the covering layer occurs.